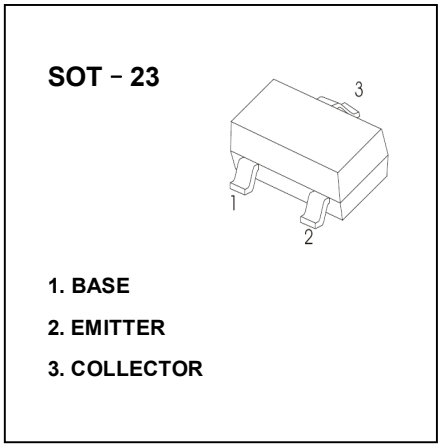
百圳君耀 BaiZhenJunYao

SOT-23 Plastic-Encapsulate Transistors

SS8550 TRANSISTOR (PNP)



FEATURES

- High Collector Current
- Complementary to SS8050

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-1.5	A
P_C	Collector Power Dissipation	300	mW
$R_{\Theta JA}$	Thermal Resistance From Junction To Ambient	417	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55～+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA, I_E=0	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-0.1mA, I_B=0	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-40V, I_E=0			-100	nA
Collector cut-off current	I_{CEO}	V_{CE}=-20V, I_B=0			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0			-100	nA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V, I_C=-100mA	120		400	
	$h_{FE(2)}$	V_{CE}=-1V, I_C=-800mA	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-800mA, I_B=-80mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-800mA, I_B=-80mA			-1.2	V
Base-emitter voltage	V_{BE}	V_{CE}=-1V, I_C=-10mA			-1	V
Transition frequency	f_T	V_{CE}=-10V,I_C=-50mA , f=30MHz	100			MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz			20	pF

CLASSIFICATION OF $h_{FE(1)}$

RANK	L	H	J
RANGE	120－200	200－350	300－400
MARKING	Y2		

Typical Characteristics